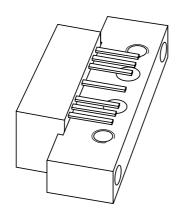
# **DISCRETE SEMICONDUCTORS**

# DATA SHEET



# **BGD502** 550 MHz, 18.5 dB gain power doubler amplifier

Product specification Supersedes data of 1995 Oct 25 2001 Nov 15





# 550 MHz, 18.5 dB gain power doubler amplifier

# **BGD502**

## **FEATURES**

- Excellent linearity
- · Extremely low noise
- Silicon nitride passivation

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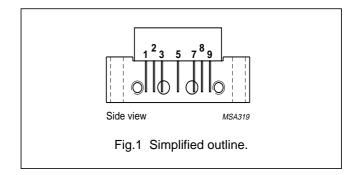
- Rugged construction
- TiPtAu metallized crystals ensure optimal reliability.

## **DESCRIPTION**

Hybrid amplifier modules for CATV systems operating over a frequency range of 40 to 550 MHz at a voltage supply of 24 V (DC).

# **PINNING - SOT115J**

PIN	DESCRIPTION	
1	input	
2, 3	common	
5	+V <sub>B</sub>	
7, 8	common	
9	output	



## **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G <sub>p</sub>	power gain	f = 50 MHz	18	19	dB
		f = 550 MHz	18.8	20.8	dB
I <sub>tot</sub>	total current consumption (DC)	V <sub>B</sub> = 24 V	_	435	mA

## **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER		MAX.	UNIT
Vi	RF input voltage		65	dBmV
T <sub>stg</sub>	storage temperature		+100	°C
T <sub>mb</sub>	operating mounting base temperature		+100	°C

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## **CHARACTERISTICS**

**Table 1** Bandwidth 40 to 550 MHz;  $V_B = 24 \text{ V}$ ;  $T_{mb} = 35 \, ^{\circ}\text{C}$ ;  $Z_S = Z_L = 75 \, \Omega$ .

SYMBOL	PARAMETER	PARAMETER CONDITIONS MIN		TYP.	MAX.	UNIT
G <sub>p</sub>	power gain	f = 50 MHz	18	_	19	dB
		f = 550 MHz	18.8	_	20.8	dB
SL	slope cable equivalent	f = 40 to 550 MHz	0.2	_	2.2	dB
FL	flatness of frequency response	f = 40 to 550 MHz	_	_	±0.3	dB
S <sub>11</sub>	input return losses	f = 40 to 80 MHz	20	_	_	dB
		f = 80 to 160 MHz	19	_	_	dB
		f = 160 to 550 MHz	18	_	_	dB
S <sub>22</sub>	output return losses	f = 40 to 80 MHz	20	_	_	dB
		f = 80 to 160 MHz	19	_	_	dB
		f = 160 to 550 MHz	18	_	_	dB
s <sub>21</sub>	phase response	f = 50 MHz	+135	_	+225	deg
СТВ	composite triple beat	77 channels flat; V <sub>o</sub> = 44 dBmV; measured at 547.25 MHz	_	-	-65	dB
X <sub>mod</sub>	cross modulation	77 channels flat; V <sub>o</sub> = 44 dBmV; measured at 55.25 MHz	_	_	-68	dB
CSO	composite second order distortion	77 channels flat; V <sub>o</sub> = 44 dBmV; measured at 548.5 MHz	-	_	-62	dB
$d_2$	second order distortion	note 1	_	_	-72	dB
Vo	output voltage	$d_{im} = -60 \text{ dB}$ ; note 2	64	_	_	dBmV
NF	noise figure	f = 550 MHz	_	_	8	dB
I <sub>tot</sub>	total current consumption (DC)	note 3	_	415	435	mA

## **Notes**

- 1. fp = 55.25 MHz; Vp = 44 dBmV; fq = 493.25 MHz; Vq = 44 dBmV; measured at fp + fq = 548.5 MHz.
- 2. Measured according to DIN45004B: fp = 540.25 MHz; Vp = Vo; fq = 547.25 MHz; Vq = Vo -6 dB; fr = 549.25 MHz; Vr = Vo -6 dB; measured at fp + fq fr = 538.25 MHz.
- 3. The module normally operates at VB = 24 V, but are able to withstand supply transients up to VB = 30 V.

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**Table 2** Bandwidth 40 to 450 MHz;  $V_B = 24$  V;  $T_{mb} = 35$  °C;  $Z_S = Z_L = 75$   $\Omega$ .

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Gp	power gain	f = 50 MHz	18	_	19	dB
		f = 450 MHz	18.6	_	20.6	dB
SL	slope cable equivalent	f = 40 to 450 MHz	0.2	_	1.8	dB
FL	flatness of frequency response	f = 40 to 450 MHz	_	_	±0.3	dB
S <sub>11</sub>	input return losses	f = 40 to 80 MHz	20	_	_	dB
		f = 80 to 160 MHz	19	_	_	dB
		f = 160 to 450 MHz	18	_	_	dB
S <sub>22</sub>	output return losses	f = 40 to 80 MHz	20	_	_	dB
		f = 80 to 160 MHz	19	_	_	dB
		f = 160 to 450 MHz	18	_	_	dB
s <sub>21</sub>	phase response	f = 50 MHz	+135	_	+225	deg
СТВ	composite triple beat	60 channels flat; V <sub>o</sub> = 46 dBmV; measured at 445.25 MHz	-	-	-67	dB
CSO	composite second order distortion	60 channels flat; V <sub>o</sub> = 46 dBmV; measured at 446.5 MHz	_	-	-60	dB
X <sub>mod</sub>	cross modulation	60 channels flat; V <sub>o</sub> = 46 dBmV; measured at 55.25 MHz	_	_	-67	dB
$d_2$	second order distortion	note 1	_	_	-75	dB
Vo	output voltage	d <sub>im</sub> = -60 dB; note 2	67	_	_	dBmV
NF	noise figure	f = 450 MHz	_	_	7	dB
I <sub>tot</sub>	total current consumption (DC)	note 3	_	415	435	mA

# **Notes**

- 1. fp = 55.25 MHz; Vp = 46 dBmV; fq = 391.25 MHz; Vq = 46 dBmV; measured at fp + fq = 446.5 MHz.
- 2. Measured according to DIN45004B: fp = 440.25 MHz; Vp = Vo; fq = 447.25 MHz; Vq = Vo 6 dB; fr = 449.25 MHz; Vr = Vo 6 dB; measured at fp + fq fr = 438.25 MHz.
- 3. The modules normally operate at VB = 24 V, but are able to withstand supply transients up to VB = 30 V.

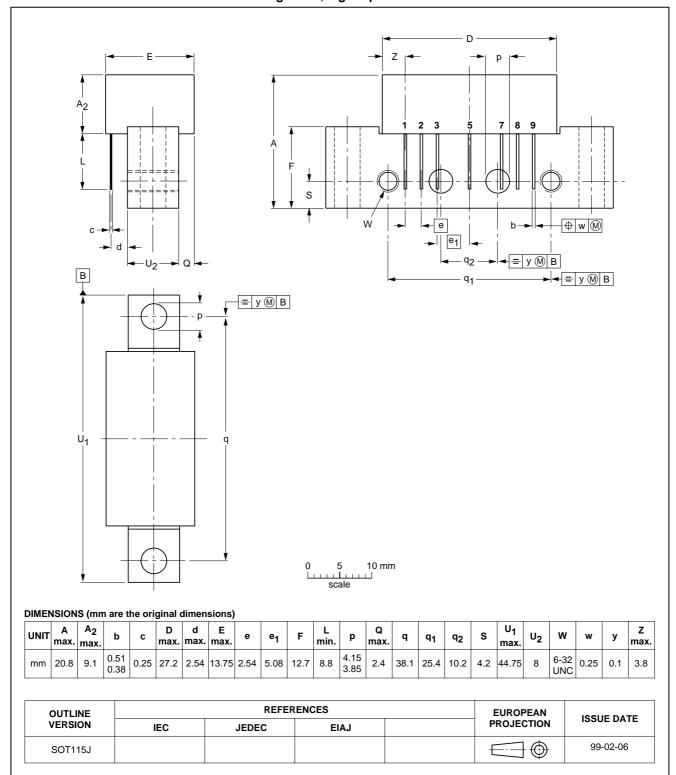
# 550 MHz, 18.5 dB gain power doubler amplifier

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## **PACKAGE OUTLINE**

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads

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#### **DATA SHEET STATUS**

DATA SHEET STATUS(1)	PRODUCT STATUS <sup>(2)</sup>	DEFINITIONS
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**NOTES** 

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